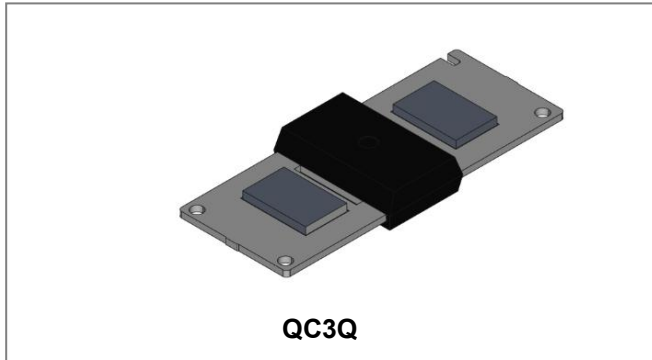


GF3545TS-1 Power Modules Schottky Rectifier



Features

- Low thermal resistance
- Lower forward voltage drop, low power loss
- Isolate Package design, ideal for heat dispersion
- High forward current capability
- Trench MOS Schottky technology
- Excellent anti-humidity
- Low profile package
- High forward surge capability
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Mechanical Data

- Case: QC3Q
- High temperature soldering guaranteed
- Heated-tool welding 260°C, 10 seconds
- Marking Code: GF3545TS-1

Maximum Ratings(Ta=25°C Unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	45	V
Average Rectified Forward Current	$I_{F(AV)}$	$T_C=123^\circ\text{C}$, In DC	35	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse, $T_J = 25^\circ\text{C}$	350	A
Rating for fusing ($t < 8.3\text{ms}$)	I^2t	$T_J = 25^\circ\text{C}$	500	A ² sec

Electrical Characteristics(Ta=25°C Unless otherwise specified)

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 35A, Pulse, $T_J = 25^\circ\text{C}$	0.48	0.52	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	0.03	0.20	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 100^\circ\text{C}$	-	12	mA
	I_{R3}	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	20	55	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	5000	-	pF

* Pulse width < 300 μs , duty cycle < 2%

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Thermal-Mechanical Specifications(Ta=25°C Unless otherwise specified)

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	IN DC Forward Mode, without reverse bias, $t \leq 1$ h	-55 to +200	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	-	1.5	°C/W

Ratings and Characteristics Curves

Figure1 Typical Forward Characteristics

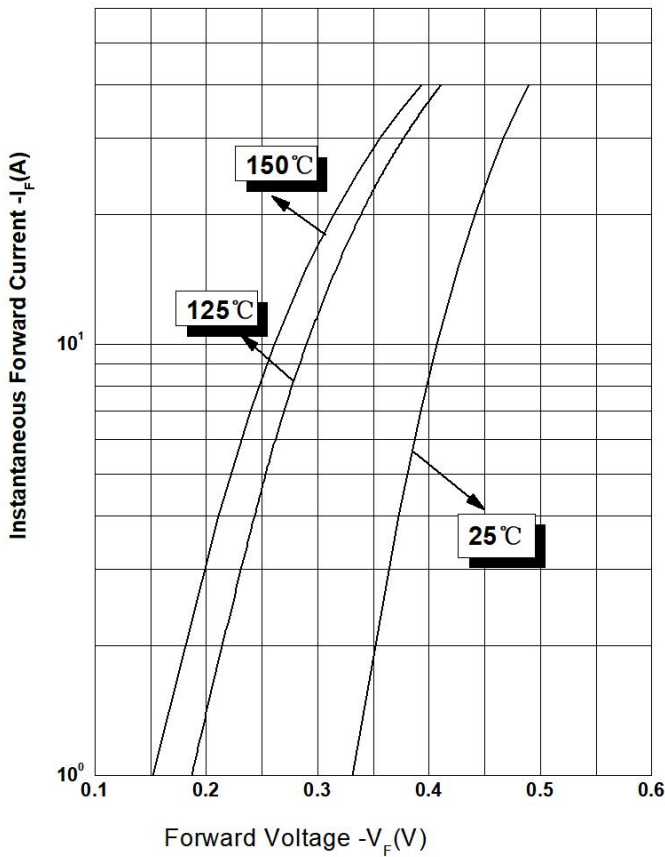


Figure 2 Typical Reverse Characteristics

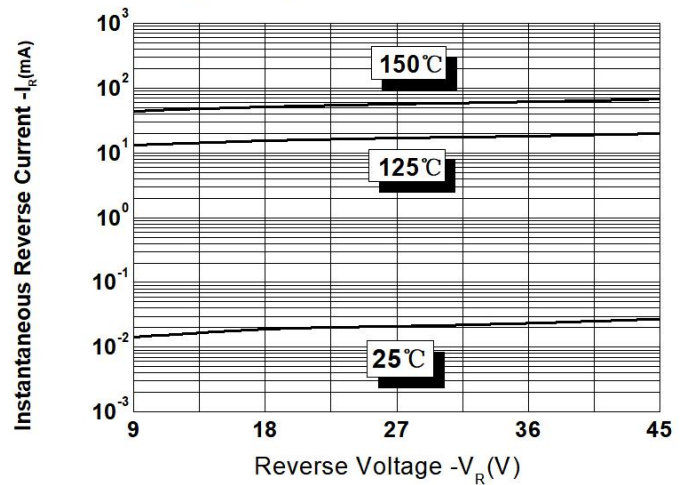
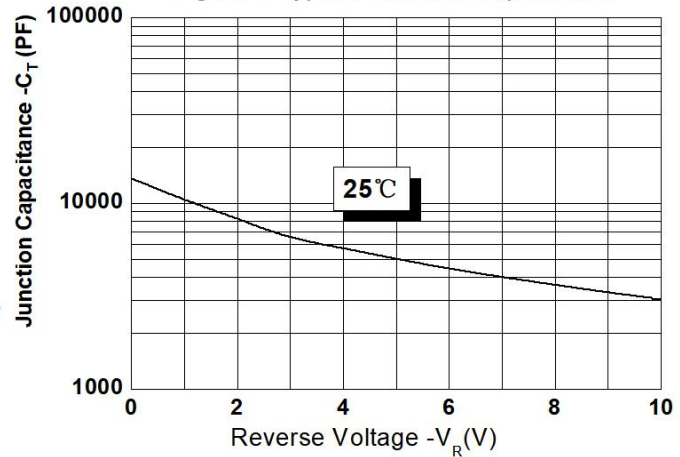


Figure 3 Typical Junction Capacitance

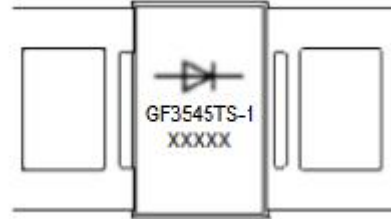


Technical Data
Data Sheet N2639, Rev.-

Ordering Information

Device	Package	Shipping
GF3545TS-1	QC3Q	32pcs/Tube

Marking Diagram



Where XXXXX is YYWWL
 GF3545TS-1 = Device Code
 YY = Year
 WW = Week
 L = Lot Number

Order P/N	Terminals	Additional
GF3545TS-1-S1	Tin Plated	None
GF3545TS-1-S2	Tin Plated	Solder Paste
GF3545TS-1-S3	Tin Plated	Solder Block
GF3545TS-1-N1	Nickel Plated	None
GF3545TS-1-N2	Nickel Plated	Solder Paste
GF3545TS-1-N3	Nickel Plated	Solder Block

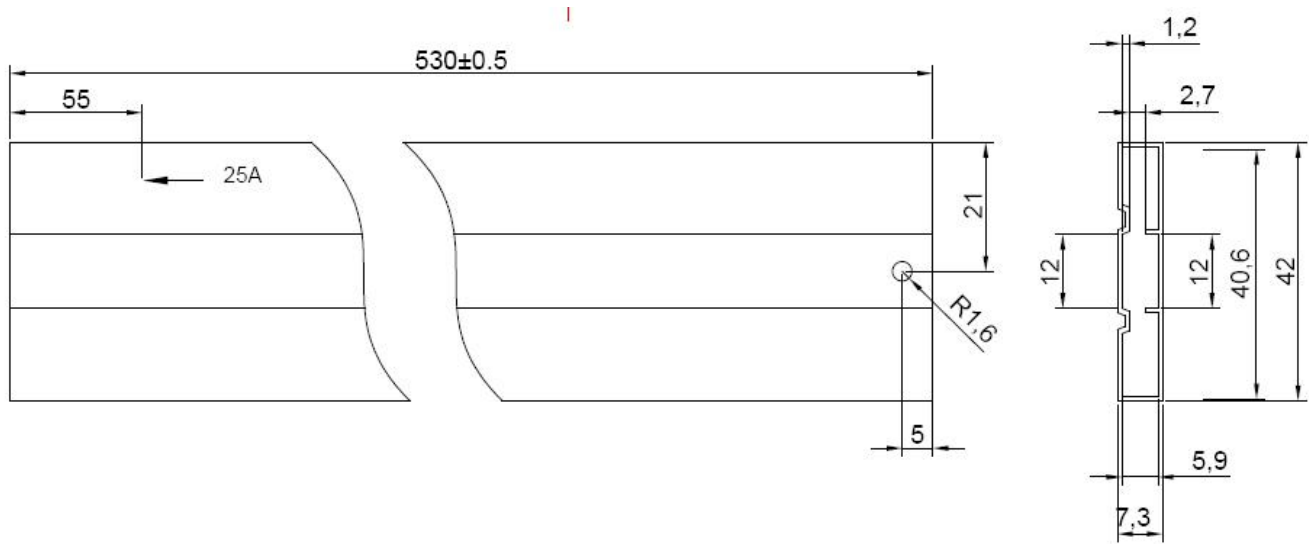


Solder Paste

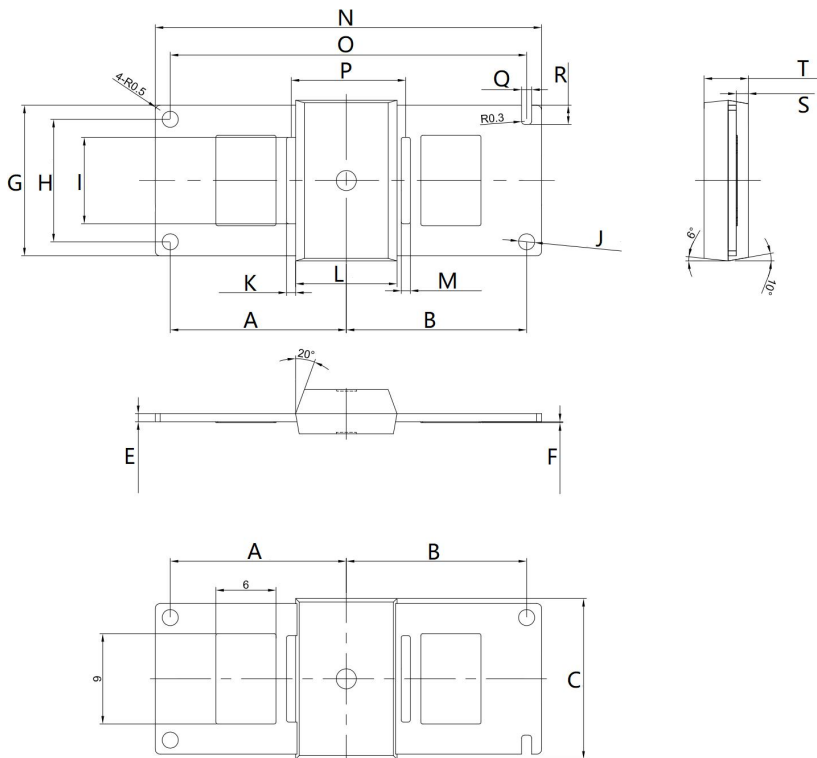


Solder Block

Tube Specification QC3Q (Millimeters)



Mechanical Dimensions QC3Q (Millimeters)



Symbol	Dimensions in millimeters		
	Min.	Typical	Max
A		17.54	
B		17.96	
C	15.90	16.00	16.10
E	0.77	0.80	0.83
F	0.08	0.10	0.12
G	14.90	15.00	15.10
H	12.15	12.20	12.25
I	8.55	8.60	8.65
J		1.60	1.70
K	0.86	0.90	0.93
L	10.00	10.10	10.20
M	0.87	0.90	0.93
N	38.40	38.50	38.60
O	35.45	35.50	35.55
P	11.32	11.42	11.52
Q		1.00	1.10
R		1.90	2.00
S	1.15	1.20	1.25
T	4.30	4.40	4.50

Technical Data
Data Sheet N2639, Rev.-

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